

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC4215

High Frequency Amplifier Applications

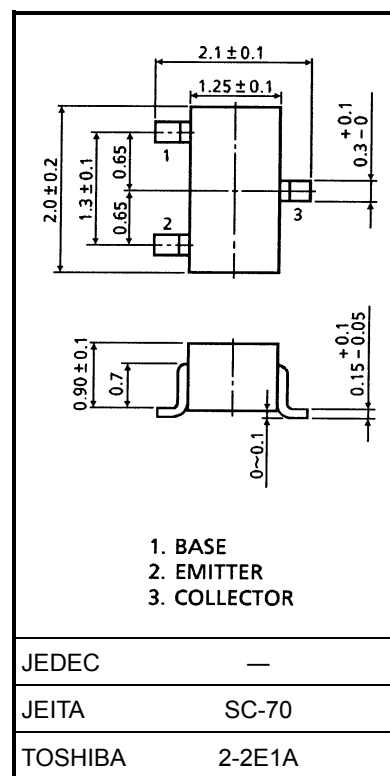
FM, RF, MIX, IF Amplifier Applications

Unit: mm

- Small reverse transfer capacitance: $C_{re} = 0.55$ pF (typ.)
- Low noise figure: NF = 2dB (typ.) (f = 100 MHz)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_C	20	mA
Base current	I_B	4	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C

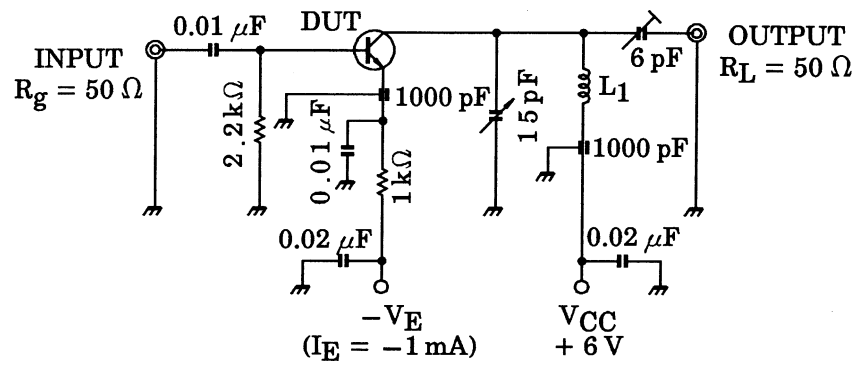


Weight: 0.006 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 40$ V, $I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4$ V, $I_C = 0$	—	—	0.5	μA
DC current gain	h_{FE} (Note)	$V_{CE} = 6$ V, $I_C = 1$ mA	40	—	200	
Reverse transfer capacitance	C_{re}	$V_{CB} = 10$ V, $f = 1$ MHz	—	0.55	—	pF
Transition frequency	f_T	$V_{CE} = 6$ V, $I_C = 1$ mA	260	550	—	MHz
Collector-base time constant	$C_c \cdot t_{bb'}$	$V_{CE} = 6$ V, $I_E = -1$ mA, $f = 30$ MHz	—	—	25	ps
Noise figure	NF	$V_{CC} = 6$ V, $I_E = -1$ mA, $f = 100$ MHz, Figure 1	—	2	5.0	dB
Power gain	G_{pe}		17	23	—	dB

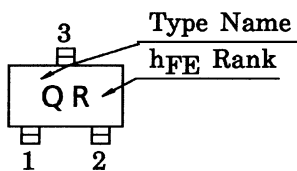
Note: h_{FE} classification R: 40~80, O: 70~140, Y: 100~200

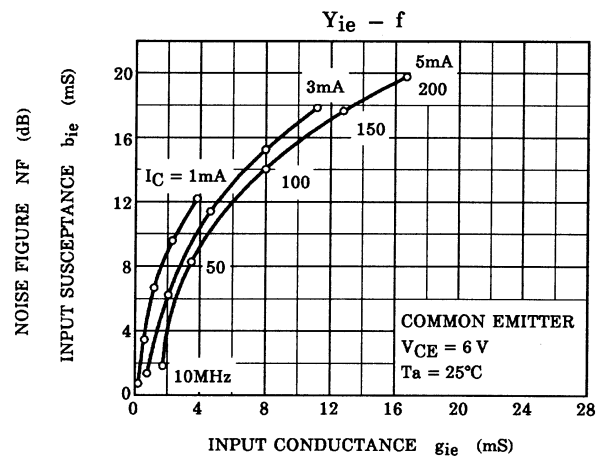
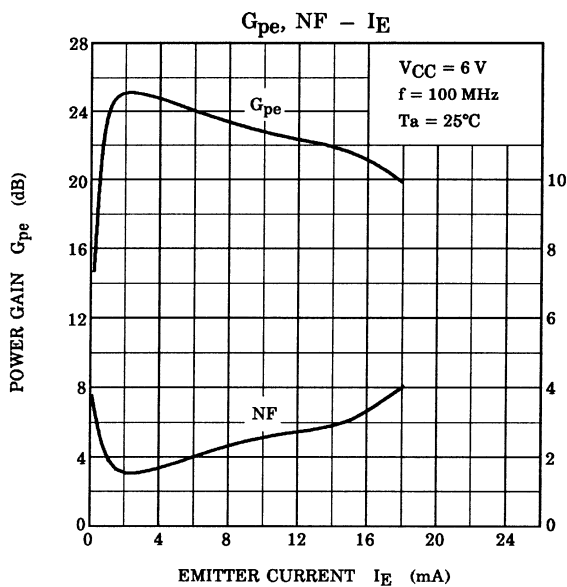
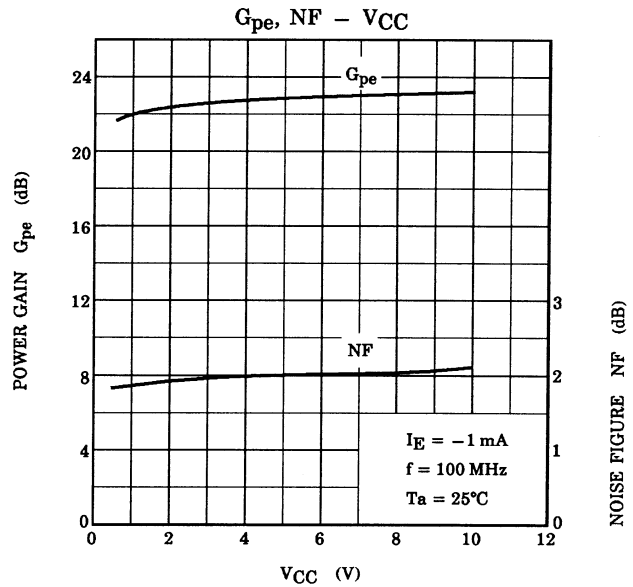
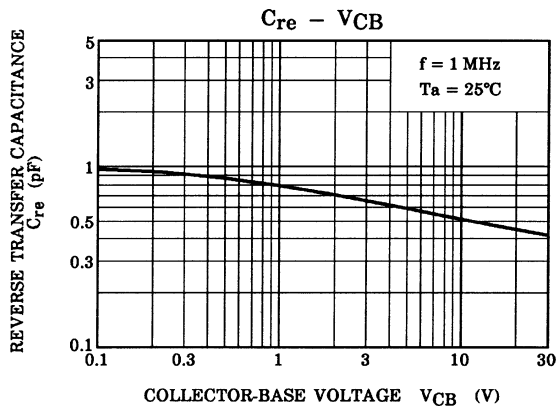
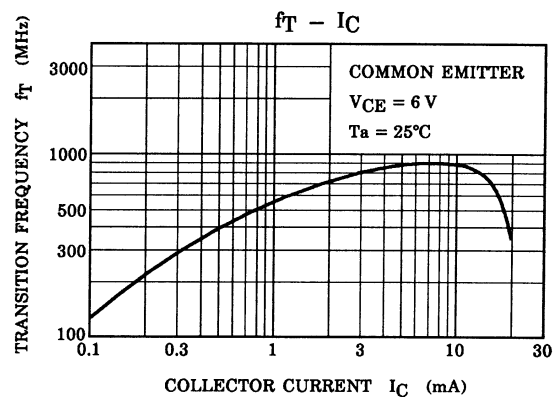
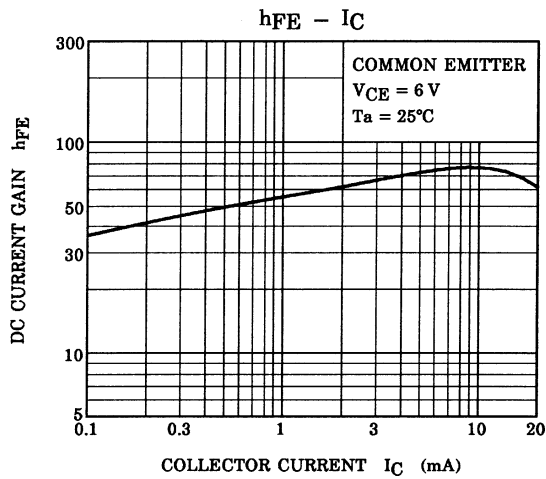


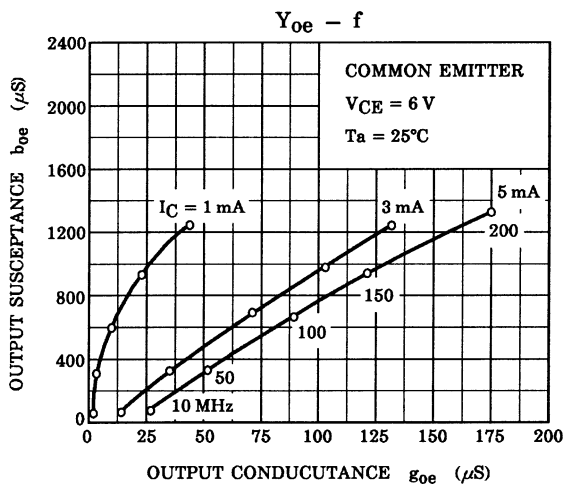
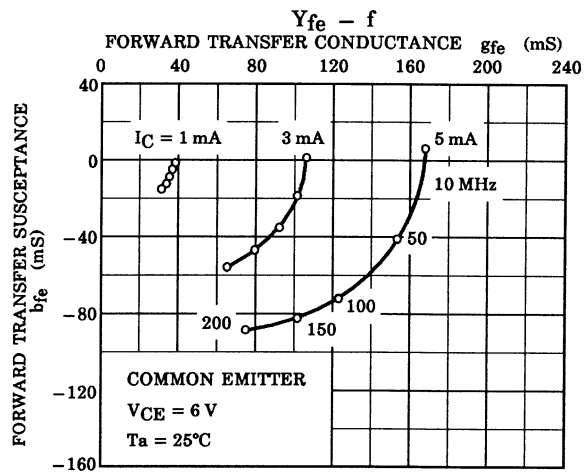
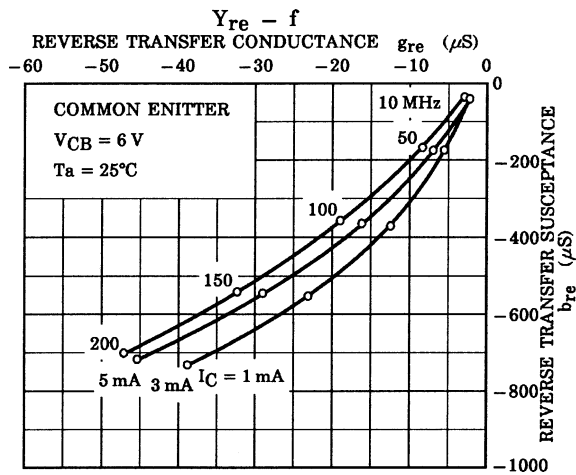
L₁: 0.8 mm ϕ silver plated copper wire, 4 T, 10 mm ID, 8 mm length

Figure 1 NF, G_{pe} Test Circuit

Marking







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